| Time stamp |
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| 2004/06/08 |
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| 2004/06/08 46-40 |
| 16:10 |
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| 2004/06/08 |
| 16:10 |
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| 2004/0 16:10 |

| 255 | 1 | diode.clm. and (m sf t r mos or | USPAT; | 2004/06/08 |
|-------|-----|---|-----------|------------|
| | | transist r). lm. and pad.clm. and esd.clm. | US-P PUB; | 16:18 |
| | | and (s r rrectifi r).clm. and (I w n ar | EPO; JPO; | |
| | | v Itage).clm. and (pad n ar10 di de near10 | DERWENT; | |
| | | (mos or mosfet or transistor)). lm. | IBM_TDB | |
| 256 | 94 | (di de near10 (transistor rm sf t orm s) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. | US-PGPUB; | 16:19 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 257 | 5 | (diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. and (scr or rectifier).clm. | US-PGPUB; | 16:20 |
| | | | EPO; JPO; | |
| | | | DERWENT: | |
| | | | IBM_TDB | |
| 258 | 3 | (diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. and (scr or rectifier).clm. | US-PGPUB; | 16:20 |
| | | and ((rectifier or scr) near10 esd) | EPO; JPO; | |
| | | , , | DERWENT; | |
| | | | IBM_TDB | |
| 259 | 1 | (diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. and (scr or rectifier).clm. | US-PGPUB; | 16:22 |
| | | and ((rectifier or scr) near10 (esd near | EPO; JPO; | |
| | | current)) | DERWENT; | |
| | | <i>"</i> | IBM_TDB | |
| . 260 | 1 | (diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. and (scr or rectifier).clm. | US-PGPUB; | 16:22 |
| | | and ((rectifier or scr or lvscr) near10 (esd | EPO; JPO; | |
| | | near current)) | DERWENT; | |
| | | | IBM_TDB | |
| 261 | 116 | ((rectifier or scr or lyscr) near10 (esd near | USPAT; | 2004/06/08 |
| | | current)) | US-PGPUB; | 16:22 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 262 | 2 | ((rectifier or scr or lvscr) near10 (esd near | USPAT; | 2004/06/08 |
| | | current)).clm. | US-PGPUB; | 16:23 |
| | 1 | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 263 | 2 | ((rectifier or scr or lvscr) near10 (esd near | USPAT; | 2004/06/08 |
| | | current) near10 (lvscr or (low near | US-PGPUB; | 16:24 |
| | | voltage))) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 264 | 730 | ((rectifier or scr or lvscr) near10 (current) | USPAT; | 2004/06/08 |
| | | near10 (lvscr or (low near voltage))) | US-PGPUB; | 16:24 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| | | | | |

| 265 | 14 | (sd near10 (rectifi r or scr or lvscr) near10 | USPAT; | 2004/06/08 |
|-----|----|--|---------------------|------------|
| | | (urr nt) n ar10 (lvscr or (l w near | US-PGPUB; | 16:25 |
| | | v Itage))) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 266 | 1 | (esd n ar10 (rectifier r cr r lvscr) n ar10 | USPAT; | 2004/06/08 |
| | | (current) near10 (lvscr or (low near | US-PGPUB; | 16:26 |
| | | voltage)) near10 (distribute or distributing | EPO; JPO; | |
| | | or distributed or distribution or pass or | DERWENT; | |
| | | passed)) | IBM_TDB | |
| 267 | 5 | ((Ivscr or (Iow near current)) near10 diode | USPAT; | 2004/06/08 |
| | | near10 esd) | US-PGPUB; | 16:27 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 268 | 0 | ((lvscr)).clm. | USPAT; | 2004/06/08 |
| | | | US-PGPUB; | 16:28 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 269 | 14 | ((Ivscr)) | USPAT; | 2004/06/08 |
| | | | US-PGPUB; | 16:28 |
| | i | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 270 | 0 | ((Ivscr)) and pad.clm. and diode.clm. | USPAT; | 2004/06/08 |
| | | | US-PGPUB; | 16:28 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| 074 | | | IBM_TDB | |
| 271 | 11 | ((Ivscr)) and pad and diode | USPAT; | 2004/06/08 |
| | | | US-PGPUB; | 16:29 |
| | | | EPO; JPO; | |
| | | | DERWENT; IBM_TDB | |
| 272 | 2 | ((Ivscr)) and (pad same diode same | USPAT; | 2004/06/08 |
| | _ | (transistor or mosfet or mos)) | US-PGPUB; | 16:30 |
| | | (translator of moster of most) | EPO; JPO; | 10.50 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 273 | 2 | (diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | - | near10 pad near10 (rectifier or scr or | US-PGPUB; | 16:34 |
| | | Isvscr) near10 esd) | EPO; JPO; | |
| | | · | DERWENT; | |
| | | | IBM_TDB | |
| 274 | o | (diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | | near10 pad near10 (rectifier or scr or | US-PGPUB; | 16:34 |
| | | lsvs r) near10 sd near10 (I w n ar2 | EPO; JPO; | |
| | | voltage)) | DERWENT; | |
| | | | IBM_TDB | |

| 275 | 0 | (diode n ar10 (transist r or m sf t or m s) | USPAT; | 2004/06/08 |
|-----|----------|--|-----------|------------|
| | | n ar10 pad near10 (rectifi r or scr or lvscr) | US-P PUB; | 16:35 |
| | | near10 esd near10 (I w near2 voltage)) | EPO; JP ; | |
| | | | DERWENT; | • |
| | | | IBM_TDB | |
| 276 | 2 | ((diode near10 (transistor or m sfet or mos) | USPAT; | 2004/06/08 |
| | | near10 pad near10 (rectifier or scr or lvscr) | US-PGPUB; | 16:38 |
| | | near10 esd) same (low near2 voltage)) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 277 | 13 | ((diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | | near10 (rectifier or scr or lyscr) near10 esd) | US-PGPUB; | 16:38 |
| | | same (low near2 voltage)) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 278 | 2 | ((diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | _ | near10 (rectifier or scr or lyscr) near10 esd) | US-PGPUB; | 16:38 |
| | | same (low near2 voltage) same (esd near | EPO; JPO; | 10.00 |
| | | current)) | DERWENT; | |
| | | Currenty | IBM_TDB | |
| 279 | 3 | ((diode near10 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| 213 | . | 1 | US-PGPUB; | 16:41 |
| | | near10 (rectifier or scr or lvscr)) same (low | , | 10:41 |
| | | near2 voltage) same (esd near current)) | EPO; JPO; | |
| | | | DERWENT; | |
| 000 | | | IBM_TDB | |
| 280 | 6 | ((diode near20 (transistor or mosfet or mos) | USPAT; | 2004/06/08 |
| | | near20 (rectifier or scr or lvscr)) same (low | US-PGPUB; | 16:42 |
| | | near2 voltage) same (esd near current)) | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 281 | 31 | ((rectifier or scr or lvscr) near10 (low near2 | USPAT; | 2004/06/08 |
| | | voltage) same (esd near current)) | US-PGPUB; | 16:42 |
| | İ | | EPO; JPO; | |
| | | | DERWENT; | |
| | _ | | IBM_TDB | |
| 282 | 5 | ((rectifier or scr or lvscr) near10 (low near2 | USPAT; | 2004/06/08 |
| | | voltage) near10 (esd near current)) | US-PGPUB; | 16:44 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| |] | | IBM_TDB | |
| 283 | 7 | ((rectifier or scr or lvscr) near20 (low near2 | USPAT; | 2004/06/08 |
| | 1 | voltage) near20 (esd near current)) | US-PGPUB; | 16:44 |
| | | | EPO; JPO; | |
| | 1 | | DERWENT; | |
| | | | IBM_TDB | |
| 284 | 1190 | ((rectifier or scr or lvscr) near20 (low near2 | USPAT; | 2004/06/08 |
| | | voltage) near20 (current)) | US-PGPUB; | 16:45 |
| | 1 | | EPO; JP ; | |
| | | | DERWENT; | |
| _ | | | IBM_TDB | |

| 285 | 8 | ((r ctifi r or scr or lvs r) n ar20 (l w n ar2 v ltag) near20 (current)).ti,ab, lm. and | USPAT; US-PGPUB; | 2004/06/08 16:45 |
|-----|----|---|-----------------------|---------------------|
| | 1 | esd.ti,ab,clm. | EP ; JPO; | 10.43 |
| | | | DERWENT; | |
| | İ | | IBM_TDB | |
| 286 | 3 | ((r tifier rscrorlvs r) near20 (I w near2 | USPAT; | 2004/06/08 |
| | | voltage) near20 (current)).ti,ab,clm. and | US-PGPUB; | 16:45 |
| | | esd.ti,ab,clm. and parasitic.ti,ab,clm. | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 287 | 1 | ((rectifier or scr or lvscr) near20 (low near2 | USPAT; | 2004/06/08 |
| | | voltage) near20 (current)).ti,ab,clm. and | US-PGPUB; | 16:47 |
| | | esd.ti,ab,clm. and parasitic.ti,ab,clm. and | EPO; JPO; | |
| | | diode.clm. | DERWENT; | |
| | | | IBM_TDB | |
| 288 | 1 | ((rectifier or scr or lvscr) near20 (low near2 | USPAT; | 2004/06/08 |
|] | | voltage) near20 (current)).ti,ab,clm. and | US-PGPUB; | 16:47 |
| | | esd.ti,ab,clm. and parasitic.ti,ab,clm. and | EPO; JPO; | |
| | | (diode near10 transistor).ti,ab,clm. | DERWENT; | |
| 289 | 94 | (diada nacudo (mas au masfat au tuansistan) | IBM_TDB | 2004/06/09 |
| 209 | 34 | (diode near10 (mos or mosfet or transistor) near10 pad).clm. | USPAT; US-PGPUB; | 2004/06/08 16:48 |
| | | near to pauj.cim. | EPO; JPO; | 10:40 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 290 | 26 | (diode near10 (mos or mosfet or transistor) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. and esd.clm. | US-PGPUB; | 16:48 |
| | | . , | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 291 | 3 | (diode near10 (mos or mosfet or transistor) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. and esd.clm. and (rectifier | US-PGPUB; | 16:50 |
| | | or scr or lvscr).clm. | EPO; JPO; | |
| | | | DERWENT; | |
| 202 | | | IBM_TDB | |
| 292 | 1 | (diode near10 (mos or mosfet or transistor) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. and esd.clm. and (rectifier or scr or lvscr).clm. and (low near | US-PGPUB; | 16:51 |
| | | voltage).clm. | EPO; JPO; DERWENT; | |
| | | voitage).ciiii. | IBM_TDB | |
| 293 | 2 | (diode near10 (mos or mosfet or transistor) | USPAT; | 2004/06/08 |
| | | near10 pad).clm. and esd.clm. and (rectifier | US-PGPUB; | 16:52 |
| | | or scr or lyscr).clm. and (low near2 | EPO; JPO; | |
| | | voltage).cim. | DERWENT; | |
| | | - | IBM_TDB | |
| 294 | 42 | (low near2 voltage) near10 (esd near | USPAT; | 2004/06/08 |
| | | current) | US-PGPUB; | 16:53 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |

| 295 | 15 | ((I w near2 v Itag) n ar10 (sd n ar | USPAT; | 2004/06/08 |
|-----|----|---|-----------|------------|
| | | urrent)) and di d .ti,ab,clm. and (m sf t | US-PGPUB; | 16:53 |
| | | r m s or transist r).ti,ab,clm. | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| 296 | 13 | ((I w near2 voltag) near10 (sd near | USPAT; | 2004/06/08 |
| | | current)) and diode.ti,ab,clm. and (mosfet | US-PGPUB; | 16:54 |
| | | or mos or transistor).ti,ab,clm. and | EPO; JPO; | |
| | | parasitic | DERWENT; | |
| | | · | IBM_TDB | |
| 297 | 6 | ((low near2 voltage) near10 (esd near | USPAT; | 2004/06/08 |
| | | current)) and diode.ti,ab,clm. and (mosfet | US-PGPUB; | 16:54 |
| | | or mos or transistor).ti,ab,clm. and | EPO; JPO; | |
| | | parasitic and pad.clm. | DERWENT; | |
| | | | IBM_TDB | |
| 298 | 4 | ((low near2 voltage) near10 (esd near | USPAT; | 2004/06/08 |
| | | current)) and diode.ti,ab,clm. and (mosfet | US-PGPUB; | 16:55 |
| | | or mos or transistor).ti,ab,clm. and | EPO; JPO; | 10100 |
| | | parasitic and pad.clm. and (rectifier or scr | DERWENT; | |
| | | or lyscr).clm. | IBM_TDB | |
| 299 | 2 | ((low near2 voltage) near10 (esd near | USPAT; | 2004/06/08 |
| 233 | - | current)) and diode.ti,ab,clm. and (mosfet | 1 | 16:57 |
| | | or mos or transistor).ti,ab,clm. and | US-PGPUB; | 16:57 |
| | | | EPO; JPO; | |
| | | parasitic.clm. and pad.clm. and (rectifier or | DERWENT; | |
| 200 | | scr or lvscr).clm. | IBM_TDB | 0004/00/00 |
| 300 | 0 | ((low near2 voltage) near10 (esd near | USPAT; | 2004/06/08 |
| | | current)).clm. and diode.ti,ab,clm. and | US-PGPUB; | 16:57 |
| | | (mosfet or mos or transistor).ti,ab,clm. and | EPO; JPO; | |
| | | parasitic.clm. and pad.clm. and (rectifier or | DERWENT; | |
| 204 | | scr or lvscr).clm. | IBM_TDB | |
| 301 | 0 | ((low near2 voltage) same (esd near | USPAT; | 2004/06/08 |
| | | current)).clm. and diode.ti,ab,clm. and | US-PGPUB; | 16:58 |
| | | (mosfet or mos or transistor).ti,ab,clm. and | EPO; JPO; | |
| | | parasitic.clm. and pad.clm. and (rectifier or | DERWENT; | |
| | _ | scr or lvscr).clm. | IBM_TDB | |
| 302 | 3 | (diode same (mos or mosfet or transistor) | USPAT; | 2004/06/08 |
| | | same parasitic same (rectifier or scr or | US-PGPUB; | 16:59 |
| | | lvscr) same (esd near current) same (low | EPO; JPO; | |
| | | near2 voltage)) | DERWENT; | |
| | | | IBM_TDB | |
| 303 | 2 | (diode same (mos or mosfet or transistor) | USPAT; | 2004/06/08 |
| | | same parasitic same (rectifier or scr or | US-PGPUB; | 16:59 |
| | | lvscr) same (esd near current) same (low | EPO; JPO; | |
| | | near2 voltage) same pad) | DERWENT; | |
| | | | IBM_TDB | |